TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7SL32F, TC7SL32FU

2-INPUT OR GATE

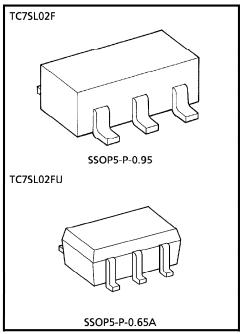
The TC7SL32 is a low voltage operative C^2MOS 2-INPUT OR GATE fabricated with silicon gate C^2MOS technology. Operating voltage (V_{CC} (opr)) is $1\sim3V$ equivalent to 1pc or 2pcs of dry cell battery and it achives low power dissipation.

The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

- High Speed t_{pd} = 10ns (Typ.)
 at V_{CC} = 3V
- Low Power Dissipation $\cdots I_{CC} = 1\mu A$ (Max.) at Ta = 25°C
- High Noise Immunity $V_{NIH} = V_{NIL}$ = 28% V_{CC} (Min.)
- Symmetrical Output Impedance ······ |I_{OH}| = I_{OL} = 1mA
- Balanced Propagation Delay Time … t_{pLH}≒t_{pHL}
- Low Voltage Operating ·················V_{CC} (opr) = 1~3.6V

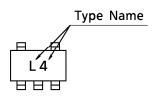


Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	-0.5~5	V
DC Input Voltage	v_{IN}	-0.5~V _{CC} +0.5	٧
DC Output Voltage	Vout	-0.5~V _{CC} + 0.5	V
Input Diode Current	lκ	± 20	mA
Output Diode Current	lok	± 20	mA
DC Output Current	IOUT	± 12.5	mΑ
DC V _{CC} / Ground Current	lcc	± 25	mΑ
Power Dissipation	PD	200	mW
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10s)	TL	260	°C

MARKING

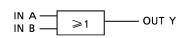


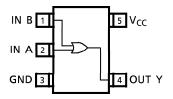
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LOGIC DIAGRAM

PIN CONNECTION (TOP VIEW)





RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	1~3.6	V
Input Voltage	V _{IN}	0~V _{CC}	V
Output Voltage	VOUT	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40~85	°C
Input Rise and Fall Time		0~1000 (V _{CC} = 1.0V)	
	t _r , t _f	0∼ 500 (V _{CC} = 1.5V)	ns
		0~ 400 (V _{CC} = 3.0V)	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC SYMBOL		TEST CIR-	TEST CONDITION V			Ta = 25°C			Ta = − 40~85°C		UNIT
		CUIT			Vcc	MIN.	TYP.	МАХ.	MIN.	MAX.	OINIT
High Loyal Input					1.0	0.75	_	_	0.75	_	
High-Level Input Voltage	VIH	—	-		1.5	1.05	—	—	1.05	 	V
Voltage					3.0	2.10	_	_	2.10	_	
Low-Level Input					1.0	—	_	0.25	—	0.25	
Voltage	V _{IL}	—		_	1.5	—	—	0.45	—	0.45	V
Voltage					3.0	_	_	0.90	—	0.90	
					1.0	0.9	1.0	l —	0.9		
High Loyal	V _{OH}		or V _{IL}	$I_{OH} = -20\mu A$	1.5	1.4	1.5	l —	1.4		v
High-Level		_			3.0	2.9	3.0	_	2.9		
Output Voltage				$I_{OH} = -1mA$	1.5	1.07	1.23	_	0.99		
				$I_{OH} = -2.6mA$	3.0	2.61	2.68	l —	2.55		
	V _{OL}		- V _{IN} = V _{IL}		1.0	—	0.0	0.1	_	0.1	
Low Lovel				$I_{OL} = 20 \mu A$	1.5	—	0.0	0.1	<u> </u>	0.1	
Low-Level Output Voltage		_			3.0	—	0.0	0.1	—	0.1	V
				I _{OL} = 1mA	1.5	_	0.23	0.31	_	0.37	
				IOL = 2.6mA	3.0	<u> </u>	0.23	0.31	<u> </u>	0.33	
Input Leakage	liki	_	V _{IN} = V _{CC}	or GND	3.6			±0.1		± 1.0	
Current	IN		AIN - ACC	OI GIND	3.0			- 0.1		± 1.0	ا ۸٫٫ ا
Quiescent Supply Current	l _{CC}	_	$V_{IN} = V_{CC}$	or GND	3.6			1.0		10.0	μΑ

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 The information contained herein is subject to change without notice.

CHARACTERISTIC SYMBO		TEST	TEST CONDITION		UNIT		
	STIVIBOL	CUIT	1231 CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition	tTLH				5.0	9.0	ns
Time	tTHL	_	_		5.0	9.0	115
Propagation	^t PLH				7.5	13.0	nc
Delay Time	t _{PHL}		1	_	7.5	13.0	ns

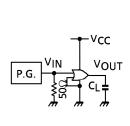
AC ELECTRICAL CHARACTERISTICS ($C_L = 25pF$, Input $t_r = t_f = 6ns$)

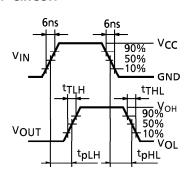
CHARACTERISTIC SYMBOL	SVMBOL	TEST	TEST CONDITION		Ta = 25°C		C	Ta = -4		
	CIR- CUIT	1231 CONDITION	V_{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT	
Output Transition	4			1.0	_	70	170	_	240	
Output Transition Time	t _{TLH}	_	_	1.5		25	45	<u> </u>	55	ns
Time	tTHL			3.0		10	15		20	
Proposition	4			1.0	_	70	170	_	210	
Propagation Delay Time	t _{PLH}	_	_	1.5	_	25	45	l —	55	ns
Delay Time	t _{PHL}			3.0	_	10	15	_	20	
Input Capacitance	CIN	_	_		_	5	10		10	
Power Dissipation	Coo		Note (1)			10				pF
Capacitance	C _{PD}		Note (1)			10				

Note (1): CpD defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

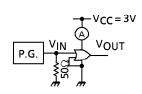
Average operating current can be obtained by the equation as follows. $I_{CC}(opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

SWITCHING CHARACTERISTICS TEST CIRCUIT





ICC (opr) TEST CIRCUIT

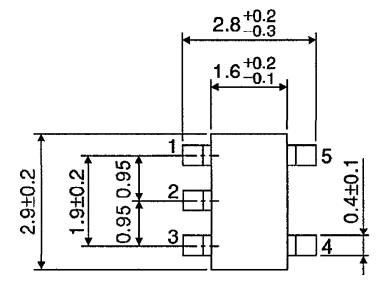


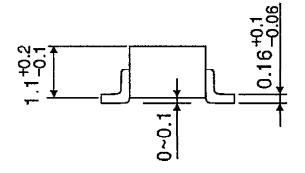
Input waveform is the same as that in case of switching characteristics test.

OUTLINE DRAWING

SSOP5-P-0.95





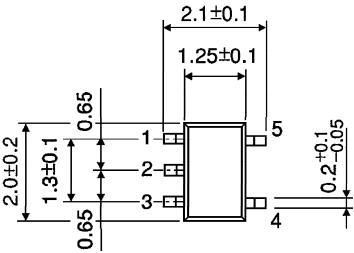


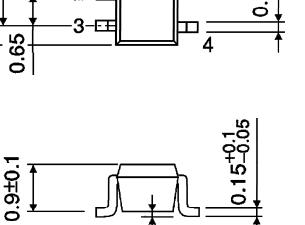
Weight: 0.016g (Typ.)

Unit: mm

OUTLINE DRAWING

SSOP5-P-0.65A





Weight: 0.006g (Typ.)